

(43) International Publication Date
6 October 2005 (06.10.2005)

PCT

(10) International Publication Number
WO 2005/093126 A1(51) International Patent Classification⁷: C23C 16/40,
16/34, 16/30, 16/448

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PCT/IB2005/000522

(22) International Filing Date: 24 February 2005 (24.02.2005)

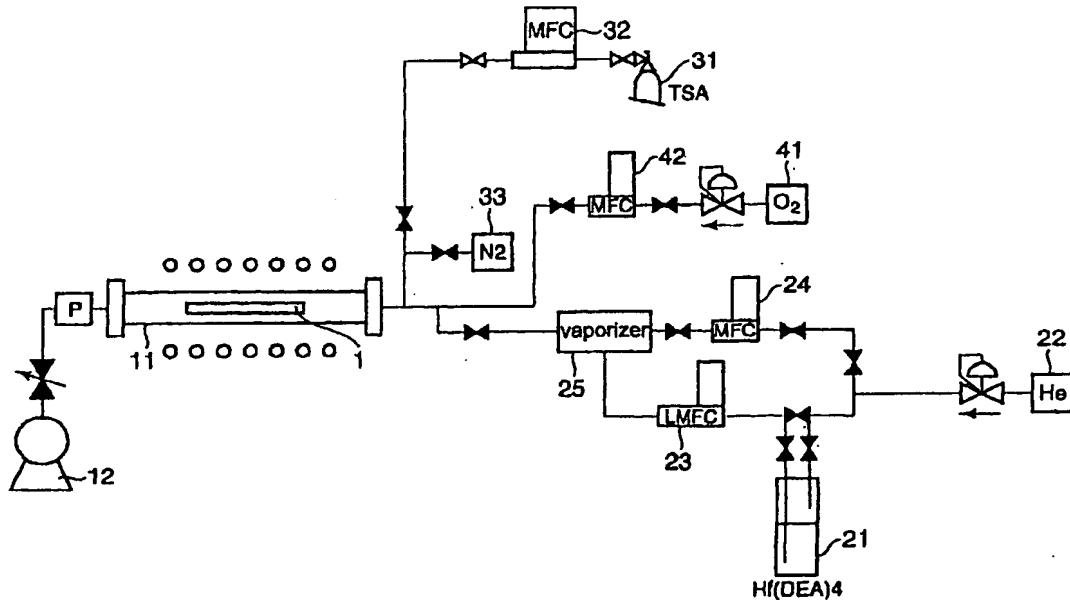
(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:

60/550,908 5 March 2004 (05.03.2004) US
2004-193710 30 June 2004 (30.06.2004) JP
10/939,269 10 September 2004 (10.09.2004) US(74) Agents: VESIN, Jacques et al.; c/o L'air Liquide S.A.,
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07 (FR).(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,*[Continued on next page]*

(54) Title: METHOD FOR FORMING DIELECTRIC OR METALLIC FILMS

(57) Abstract: Method for producing a metal silicon (oxy)nitride by introducing a carbon-free silicon source (for example, $(\text{SiH}_3)_3\text{N}$), a metal precursor with the general formula MX_n (for example, $\text{Hf}(\text{NEt}_2)_4$), and an oxidizing agent (for example, O_2) into a CVD chamber and reacting same at the surface of a substrate. MsiN , MSiO and/or MSiON films may be obtained. These films are useful as high k dielectrics films.

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MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(84) **Designated States (unless otherwise indicated, for every kind of regional protection available):** ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,